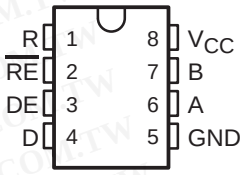
SLLS040H – AUGUST 1987 – REVISED JUNE 2000

- **Meet or Exceed the Requirements of TIA/EIA-422-B, TIA/EIA-485-A† and ITU Recommendations V.11 and X.27**
- **Operate at Data Rates up to 35 Mbaud**
- **Four Skew Limits Available:**
  SN65ALS176 . . . 15 ns
  SN75ALS176 . . . 10 ns
  SN75ALS176A . . . 7.5 ns
  SN75ALS176B . . . 5 ns
- **Designed for Multipoint Transmission on Long Bus Lines in Noisy Environments**
- **Low Supply-Current Requirements . . . 30 mA Max**
- **Wide Positive and Negative Input/Output Bus-Voltage Ranges**
- **Thermal Shutdown Protection**
- **Driver Positive and Negative Current Limiting**
- **Receiver Input Hysteresis**
- **Glitch-Free Power-Up and Power-Down Protection**
- **Receiver Open-Circuit Fail-Safe Design**

D OR P PACKAGE
(TOP VIEW)



description

The SN65ALS176 and SN75ALS176 series differential bus transceivers are designed for bidirectional data communication on multipoint bus transmission lines. They are designed for balanced transmission lines and meet TIA/EIA-422-B, TIA/EIA-485-A, and ITU Recommendations V.11 and X.27.

The SN65ALS176 and SN75ALS176 series combine a 3-state, differential line driver and a differential input line receiver, both of which operate from a single 5-V power supply. The driver and receiver have active-high and active-low enables, respectively, that can be connected together externally to function as a direction control. The driver differential outputs and the receiver differential inputs are connected internally to form a differential input/output (I/O) bus port that is designed to offer minimum loading to the bus when the driver is disabled or V_{CC} = 0. This port features wide positive and negative common-mode voltage ranges, making the device suitable for party-line applications.

The SN65ALS176 is characterized for operation from –40°C to 85°C. The SN75ALS176 series is characterized for operation from 0°C to 70°C.

† These devices meet or exceed the requirements of TIA/EIA-485-A, except for the Generator Contention Test (para. 3.4.2) and the Generator Current Limit (para. 3.4.3). The applied test voltage ranges are –6 V to 8 V for the SN75ALS176, SN75ALS176A, and SN75ALS176B and –4 V to 8 V for the SN65ALS180.

AVAILABLE OPTIONS

T_A	$t_{sk(lim)}$†	PACKAGED DEVICES	
		SMALL OUTLINE (D)‡	PLASTIC DIP (P)
0°C to 70°C	10	SN75ALS176D	SN75ALS176P
	7.5	SN75ALS176AD	SN75ALS176AP
	5	SN75ALS176BD	SN75ALS176BP
–40°C to 85°C	15	SN65ALS176D	SN65ALS176P

† This is the maximum range that the driver or receiver delay times vary over temperature, V_{CC}, and process (device to device).
‡ The D package is available taped and reeled. Add the suffix R to the device type (e.g., SN75ALS176DR).

Function Tables

DRIVER

INPUT D	ENABLE DE	OUTPUTS A	OUTPUTS B
H	H	H	L
L	H	L	H
X	L	Z	Z

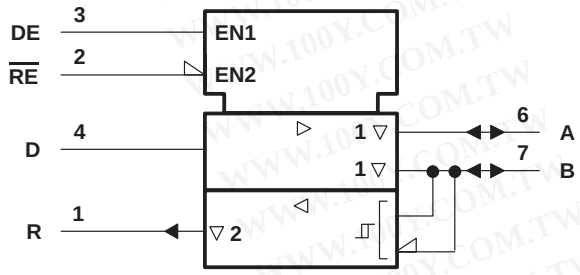
H = high level, L = low level, X = irrelevant, Z = high impedance

RECEIVER

DIFFERENTIAL INPUTS A–B	ENABLE $\overline{RE}$	OUTPUT R
$V_{ID} \geq 0.2$ V	L	H
-0.2 V $< V_{ID} < 0.2$ V	L	?
$V_{ID} \leq -0.2$ V	L	L
X	H	Z
Inputs open	L	H

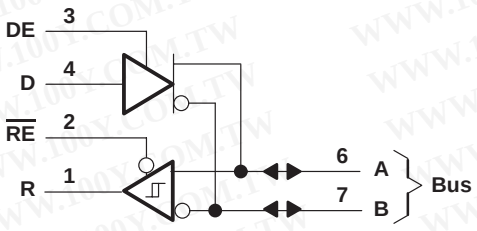
H = high level, L = low level, X = irrelevant, Z = high impedance

logic symbol§

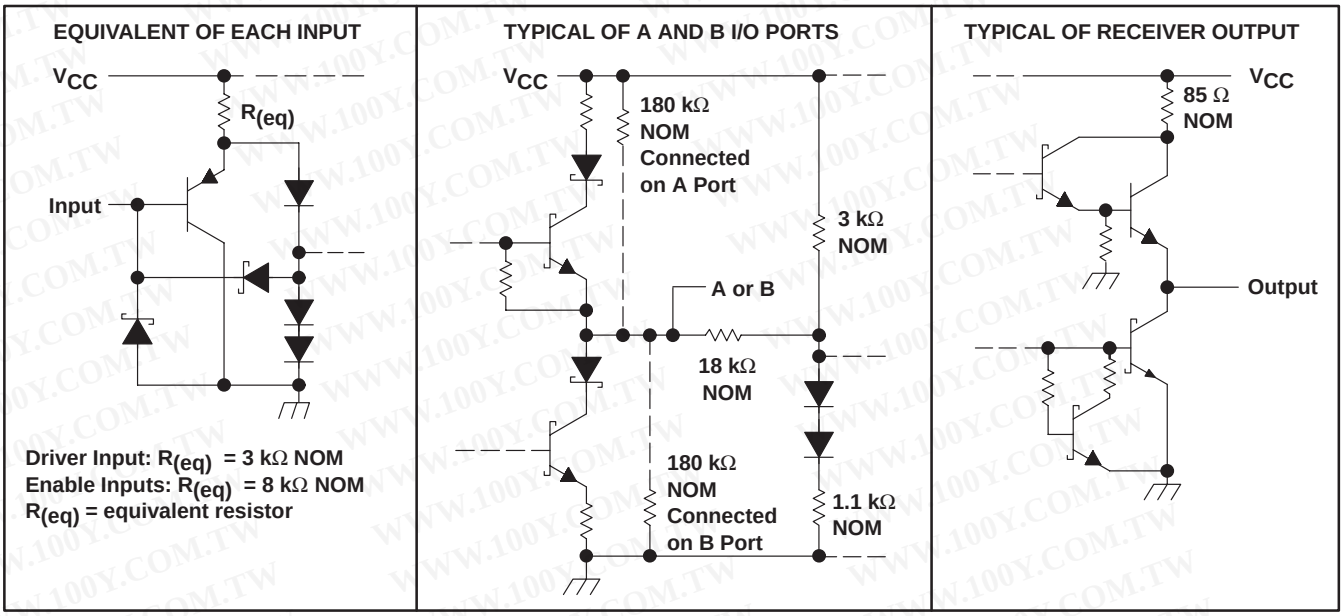


§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{CC} (see Note 1)	7 V
Voltage range at any bus terminal	–7 V to 12 V
Enable input voltage, V_I	5.5 V
Package thermal impedance, θ_{JA} (see Note 2): D package	97°C/W
P package	85°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential I/O bus voltage, are with respect to network ground terminal.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}		4.75	5	5.25	V
Input voltage at any bus terminal (separately or common mode), V_I or V_{IC}				12	V
				–7	
High-level input voltage, V_{IH}	D, DE, and $\overline{RE}$	2			V
Low-level input voltage, V_{IL}	D, DE, and $\overline{RE}$			0.8	V
Differential input voltage, V_{ID} (see Note 3)				±12	V
High-level output current, I_{OH}	Driver			–60	mA
	Receiver			–400	µA
Low-level output current, I_{OL}	Driver			60	mA
	Receiver			8	
Operating free-air temperature, T_A	SN65ALS176	–40		85	°C
	SN75ALS176 series	0		70	

NOTE 3: Differential input/output bus voltage is measured at the noninverting terminal A with respect to the inverting terminal B.

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS†		MIN	TYP‡	MAX	UNIT
V_{IK}	Input clamp voltage	I_I = –18 mA				–1.5	V
V_O	Output voltage	I_O = 0		0		6	V
$\|V_{OD1}\|$	Differential output voltage	I_O = 0		1.5		6	V
$\|V_{OD2}\|$	Differential output voltage	R_L = 100 Ω,	See Figure 1	1/2V_{OD1} or 2§			V
		R_L = 54 Ω,	See Figure 1	1.5	2.5	5	V
V_{OD3}	Differential output voltage	V_{test} = –7 V to 12 V,	See Figure 2	1.5		5	V
$\Delta\|V_{OD}\|$	Change in magnitude of differential output voltage¶	R_L = 54 Ω or 100 Ω,	See Figure 1			±0.2	V
V_{OC}	Common-mode output voltage	R_L = 54 Ω or 100 Ω,	See Figure 1			3 –1	V
$\Delta\|V_{OC}\|$	Change in magnitude of common-mode output voltage¶	R_L = 54 Ω or 100 Ω,	See Figure 1			±0.2	V
I_O	Output current	Outputs disabled (see Note 4)	V_O = 12 V			1	mA
			V_O = –7 V			–0.8	
I_{IH}	High-level input current	V_I = 2.4 V				20	µA
I_{IL}	Low-level input current	V_I = 0.4 V				–400	µA
I_{OS}	Short-circuit output current#	V_O = –4 V	SN65ALS176			–250	mA
		V_O = –6 V	SN75ALS176			–250	
		V_O = 0				–150	
		V_O = V_{CC}				250	
		V_O = 8 V				250	
I_{CC}	Supply current	No load	Outputs enabled		23	30	mA
			Outputs disabled		19	26	

† The power-off measurement in TIA/EIA-422-B applies to disabled outputs only and is not applied to combined inputs and outputs.
‡ All typical values are at V_{CC} = 5 V and T_A = 25°C.
§ The minimum V_{OD2} with a 100-Ω load is either 1/2 V_{OD1} or 2 V, whichever is greater.
¶ $\Delta|V_{OD}|$ and $\Delta|V_{OC}|$ are the changes in magnitude of V_{OD} and V_{OC}, respectively, that occur when the input is changed from one logic state to the other.
# Duration of the short circuit should not exceed one second for this test.
NOTE 4: This applies for power on and power off. Refer to TIA/EIA-485-A for exact conditions. The TIA/EIA-422-B limit does not apply for a combined driver and receiver terminal.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

SN65ALS176

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
$t_{d(OD)}$	Differential output delay time	R_L = 54 Ω,	C_L = 50 pF,	See Figure 3			15	ns
$t_{sk(p)}$	Pulse skew‡	R_L = 54 Ω,	C_L = 50 pF,	See Figure 3		0	2	ns
$t_{sk(lim)}$	Pulse skew§	R_L = 54 Ω,	C_L = 50 pF,	See Figure 3			15	ns
$t_{t(OD)}$	Differential output transition time	R_L = 54 Ω,	C_L = 50 pF,	See Figure 3		8		ns
t_{PZH}	Output enable time to high level	R_L = 110 Ω,	C_L = 50 pF,	See Figure 4			80	ns
t_{PZL}	Output enable time to low level	R_L = 110 Ω,	C_L = 50 pF,	See Figure 5			30	ns
t_{PHZ}	Output disable time from high level	R_L = 110 Ω,	C_L = 50 pF,	See Figure 4			50	ns
t_{PLZ}	Output disable time from low level	R_L = 110 Ω,	C_L = 50 pF,	See Figure 5			30	ns

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡ Pulse skew is defined as the $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
§ Skew limit is the maximum difference in propagation delay times between any two channels of any two devices.

SN75ALS176, SN75ALS176A, SN75ALS176B

PARAMETER			TEST CONDITIONS			MIN	TYP†	MAX	UNIT
$t_{d(OD)}$	Differential output delay time	'ALS176	R_L = 54 Ω,	C_L = 50 pF,	See Figure 3	3	8	13	ns
		'ALS176A				4	7	11.5	
		'ALS176B				5	8	10	
$t_{sk(p)}$	Pulse skew‡		R_L = 54 Ω,	C_L = 50 pF,	See Figure 3		0	2	ns
$t_{sk(lim)}$	Pulse skew§	'ALS176	R_L = 54 Ω,	C_L = 50 pF,	See Figure 3			10	ns
		'ALS176A						7.5	
		'ALS176B						5	
$t_{t(OD)}$	Differential output transition time		R_L = 54 Ω,	C_L = 50 pF,	See Figure 3		8		ns
t_{PZH}	Output enable time to high level		R_L = 110 Ω,	C_L = 50 pF,	See Figure 4		23	50	ns
t_{PZL}	Output enable time to low level		R_L = 110 Ω,	C_L = 50 pF,	See Figure 5		14	20	ns
t_{PHZ}	Output disable time from high level		R_L = 110 Ω,	C_L = 50 pF,	See Figure 4		20	35	ns
t_{PLZ}	Output disable time from low level		R_L = 110 Ω,	C_L = 50 pF,	See Figure 5		8	17	ns

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡ Pulse skew is defined as the $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
§ Skew limit is the maximum difference in propagation delay times between any two channels of any two devices.

SYMBOL EQUIVALENTS

DATA-SHEET PARAMETER	TIA/EIA-422-B	TIA/EIA-485-A
V_O	V_{oa}, V_{ob}	V_{oa}, V_{ob}
$\|V_{OD1}\|$	V_o	V_o
$\|V_{OD2}\|$	V_t (R_L = 100 Ω)	V_t (R_L = 54 Ω)
$\|V_{OD3}\|$	None	V_t (test termination measurement 2)
$\Delta\|V_{OD}\|$	$\|\|V_t\| - \|\overline{V_t}\|\|$	$\|\|V_t\| - \|\overline{V_t}\|\|$
V_{OC}	$\|V_{os}\|$	$\|V_{os}\|$
$\Delta\|V_{OC}\|$	$\|V_{os} - \overline{V_{os}}\|$	$\|V_{os} - \overline{V_{os}}\|$
I_{OS}	$\|I_{sa}\|$, $\|I_{sb}\|$	None
I_O	$\|I_{xa}\|$, $\|I_{xb}\|$	I_{ia}, I_{ib}

RECEIVER SECTION

electrical characteristics over recommended ranges of common-mode input voltage, supply voltage, and operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	V_O = 2.7 V,	I_O = –0.4 mA			0.2	V
V_{IT-}	Negative-going input threshold voltage	V_O = 0.5 V,	I_O = 8 mA	–0.2‡			V
V_{hys}	Hysteresis voltage ($V_{IT+} - V_{IT-}$)				60		mV
V_{IK}	Enable-input clamp voltage	I_I = –18 mA				–1.5	V
V_{OH}	High-level output voltage	V_{ID} = 200 mV, See Figure 6	I_{OH} = –400 µA,	2.7			V
V_{OL}	Low-level output voltage	V_{ID} = –200 mV, See Figure 6	I_{OL} = 8 mA,			0.45	V
I_{OZ}	High-impedance-state output current	V_O = 0.4 V to 2.4 V				±20	µA
V_I	Line input current	Other input = 0 V (see Note 5)	V_I = 12 V			1	mA
			V_I = –7 V			–0.8	
I_{IH}	High-level-enable input current	V_{IH} = 2.7 V				20	µA
I_{IL}	Low-level-enable input current	V_{IL} = 0.4 V				–100	µA
r_I	Input resistance			12	20		kΩ
I_{OS}	Short-circuit output current	V_{ID} = 200 mV,	V_O = 0	–15		–85	mA
I_{CC}	Supply current	No load	Outputs enabled		23	30	mA
			Outputs disabled		19	26	

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡ The algebraic convention, in which the less positive (more negative) limit is designated minimum, is used in this data sheet for common-mode input voltage and threshold voltage levels only.
NOTE 5: This applies for power on and power off. Refer to TIA/EIA-485-A for exact conditions.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

SN65ALS176

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
t_{pd}	Propagation time	V_{ID} = –1.5 V to 1.5 V, See Figure 7	C_L = 15 pF,			25	ns
$t_{sk(p)}$	Pulse skew§	V_{ID} = –1.5 V to 1.5 V, See Figure 7	C_L = 15 pF,		0	2	ns
$t_{sk(lim)}$	Pulse skew¶	R_L = 54 Ω, See Figure 3	C_L = 50 pF,			15	ns
t_{PZH}	Output enable time to high level	C_L = 15 pF,	See Figure 8		11	18	ns
t_{PZL}	Output enable time to low level	C_L = 15 pF,	See Figure 8		11	18	ns
t_{PHZ}	Output disable time from high level	C_L = 15 pF,	See Figure 8			50	ns
t_{PLZ}	Output disable time from low level	C_L = 15 pF,	See Figure 8			30	ns

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
§ Pulse skew is defined as the $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
¶ Skew limit is the maximum difference in propagation delay times between any two channels of any two devices.

SN75ALS176, SN75ALS176A, SN75ALS176B

PARAMETER			TEST CONDITIONS		MIN	TYP†	MAX	UNIT
t_{pd}	Propagation time	'ALS176	V_{ID} = –1.5 V to 1.5 V, See Figure 7	C_L = 15 pF,	9	14	19	ns
		'ALS176A			10.5	14	18	
		'ALS176B			11.5	13	16.5	
$t_{sk(p)}$	Pulse skew‡		V_{ID} = –1.5 V to 1.5 V, See Figure 7	C_L = 15 pF,		0	2	ns
$t_{sk(lim)}$	Pulse skew§	'ALS176	R_L = 54 Ω, See Figure 3	C_L = 50 pF,			10	ns
		'ALS176A					7.5	
		'ALS176B					5	
t_{PZH}	Output enable time to high level		C_L = 15 pF,	See Figure 8		7	14	ns
t_{PZL}	Output enable time to low level		C_L = 15 pF,	See Figure 8		20	35	ns
t_{PHZ}	Output disable time from high level		C_L = 15 pF,	See Figure 8		20	35	ns
t_{PLZ}	Output disable time from low level		C_L = 15 pF,	See Figure 8		8	17	ns

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡ Pulse skew is defined as the $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
§ Skew limit is the maximum difference in propagation delay times between any two channels of any two devices.

PARAMETER MEASUREMENT INFORMATION

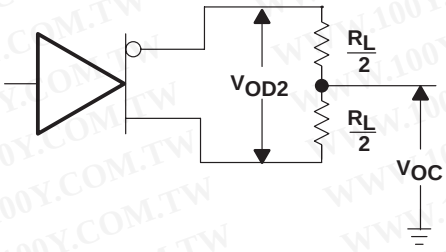


Figure 1. Driver V_{OD2} and V_{OC}

PARAMETER MEASUREMENT INFORMATION

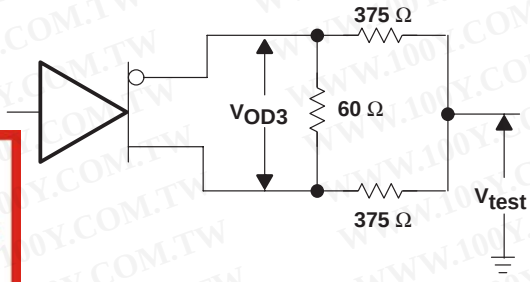
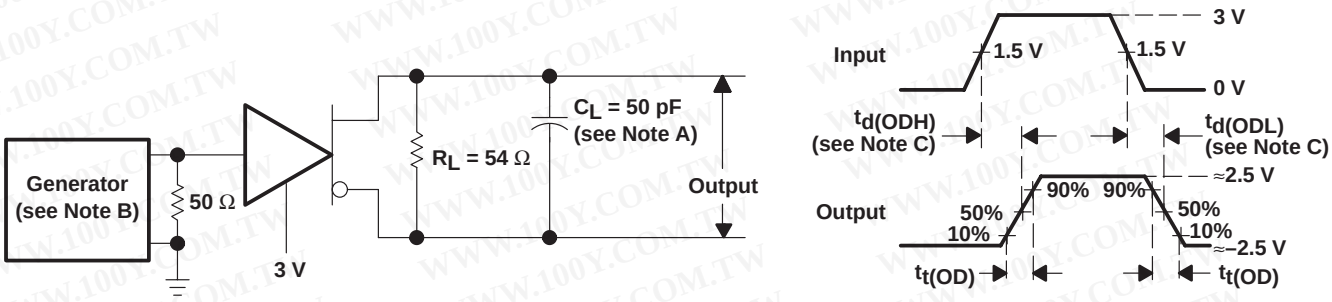
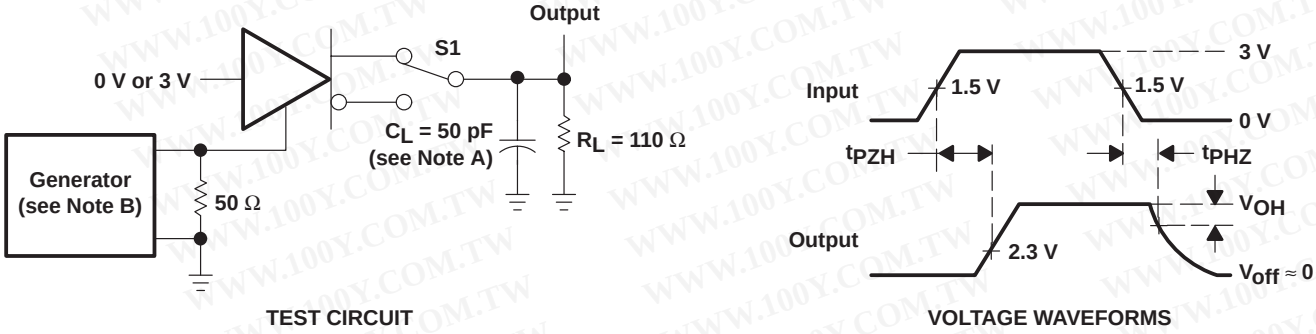


Figure 2. Driver V_{OD3}



NOTES: A. C_L includes probe and jig capacitance.
B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
C. $t_{d(OD)} = t_{d(ODH)}$ or $t_{d(ODL)}$

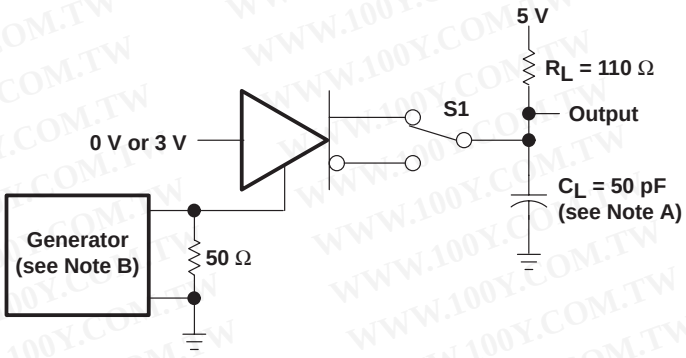
Figure 3. Driver Test Circuit and Voltage Waveforms



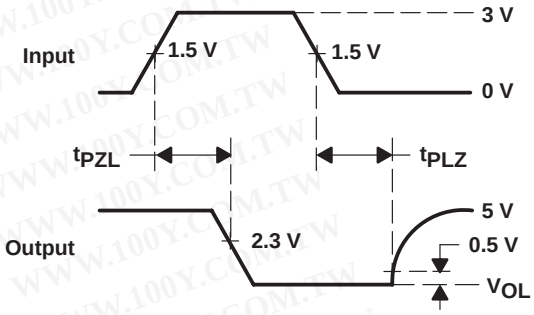
NOTES: A. C_L includes probe and jig capacitance.
B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.

Figure 4. Driver Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.

Figure 5. Driver Test Circuit and Voltage Waveforms

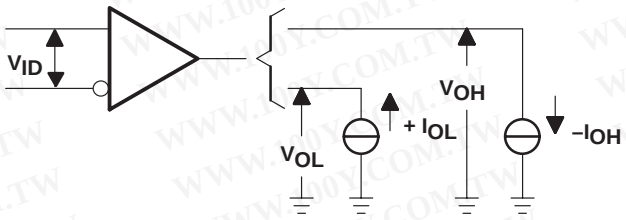
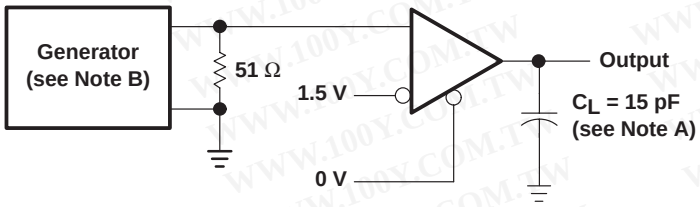
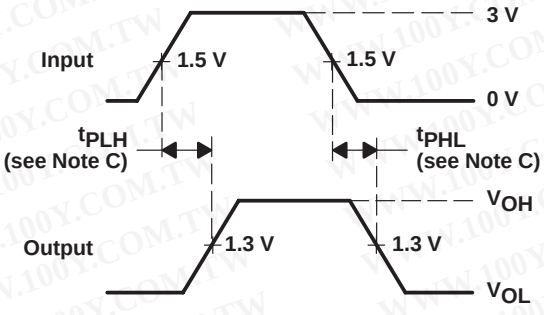


Figure 6. Receiver V_{OH} and V_{OL} Test Circuit



TEST CIRCUIT

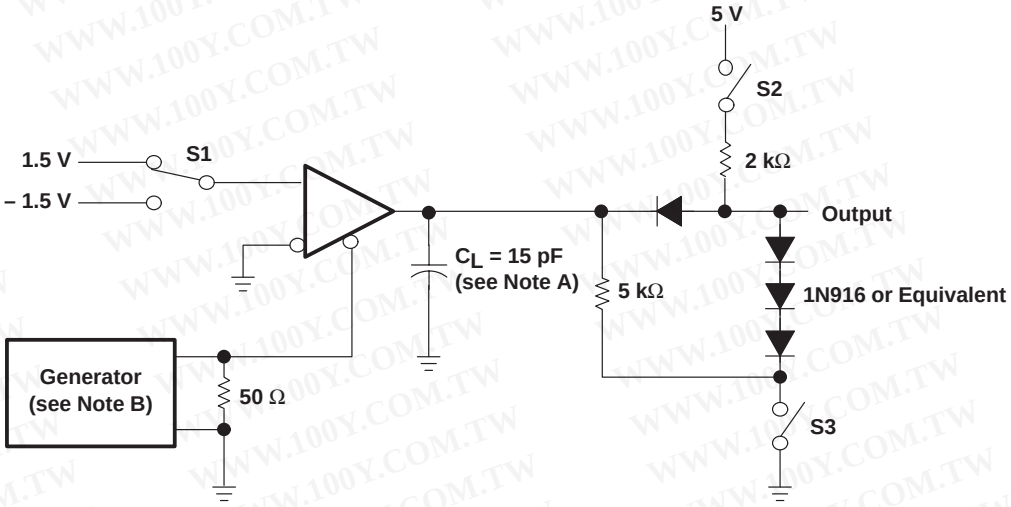


VOLTAGE WAVEFORMS

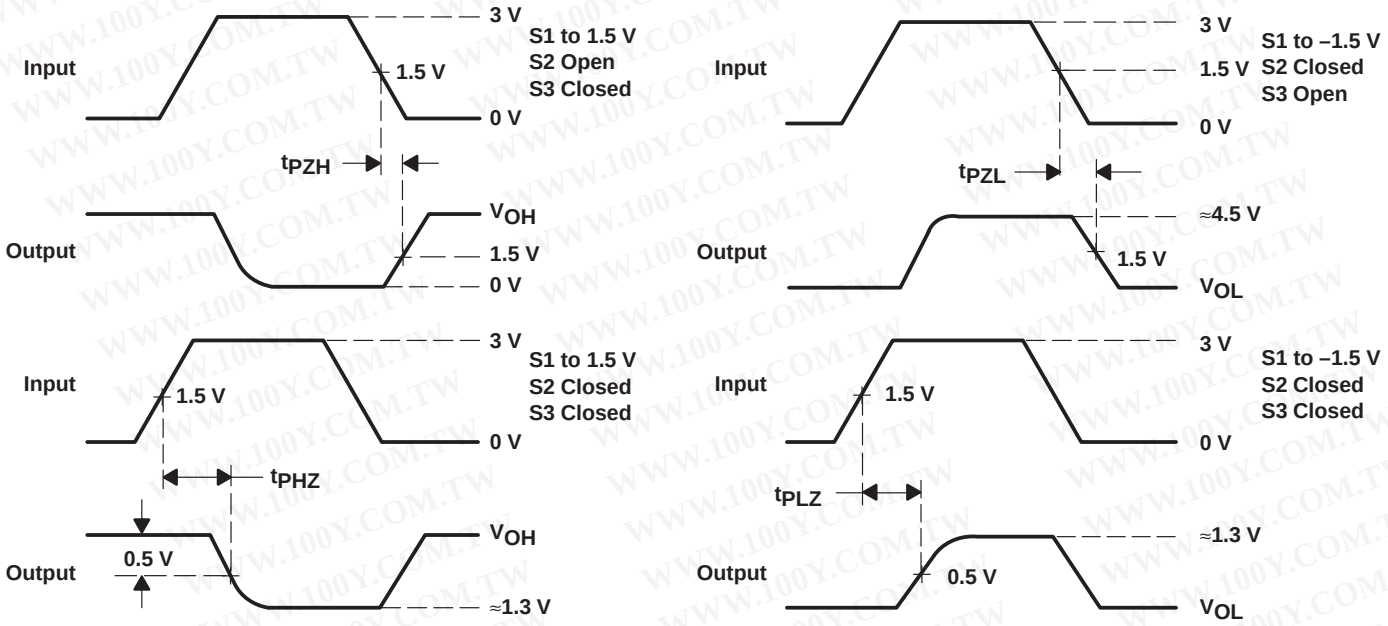
NOTES: A. C_L includes probe and jig capacitance.
B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
C. t_{pd} = t_{PLH} or t_{PHL}

Figure 7. Receiver Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.

Figure 8. Receiver Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS†

DRIVER
HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

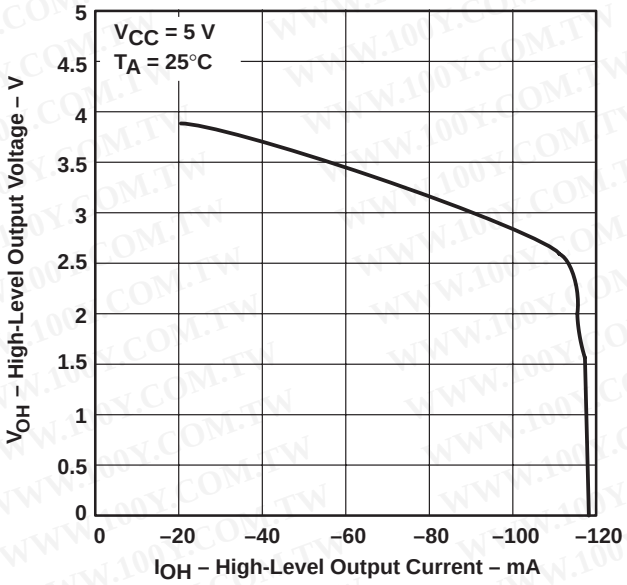


Figure 9

DRIVER
LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

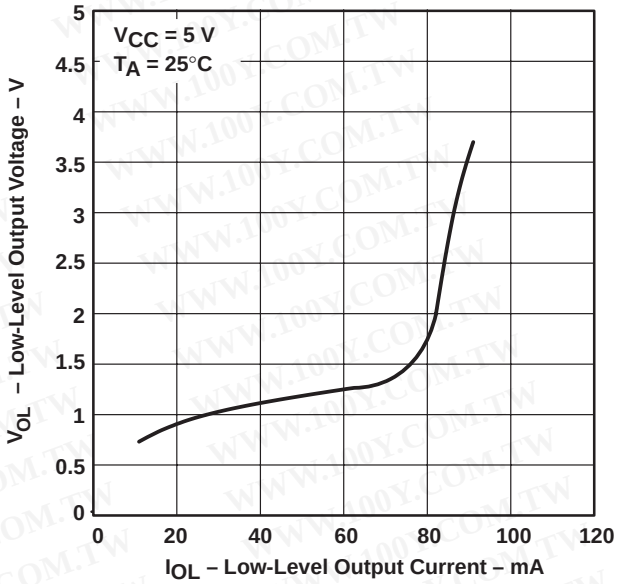


Figure 10

DRIVER
DIFFERENTIAL OUTPUT VOLTAGE
vs
OUTPUT CURRENT

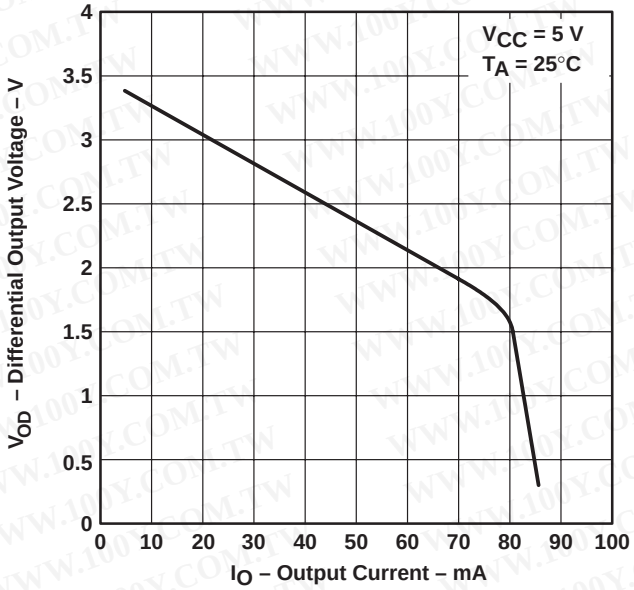


Figure 11

† Operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied.

RECEIVER TYPICAL CHARACTERISTICS†

RECEIVER
HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

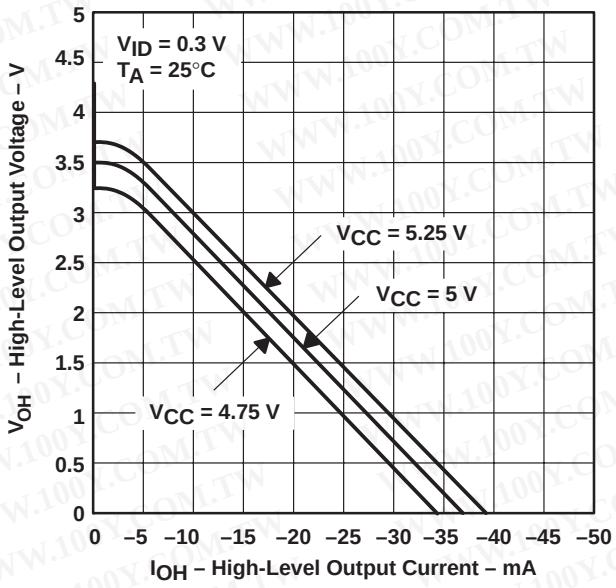


Figure 12

RECEIVER
HIGH-LEVEL OUTPUT VOLTAGE
vs
FREE-AIR TEMPERATURE

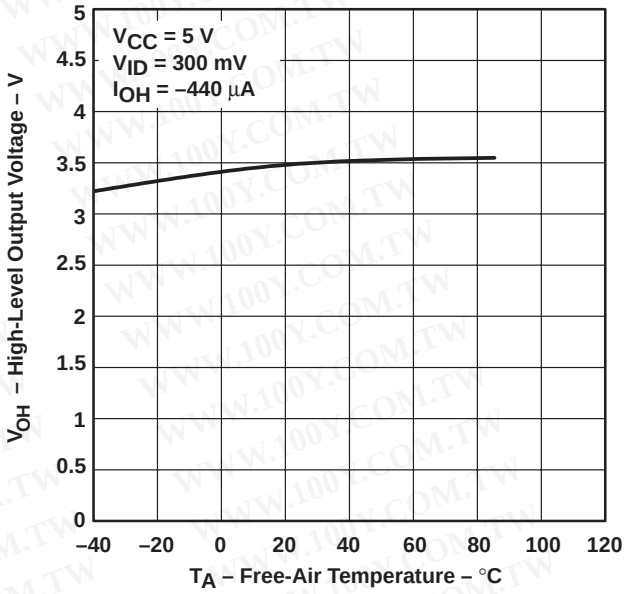


Figure 13

RECEIVER
LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

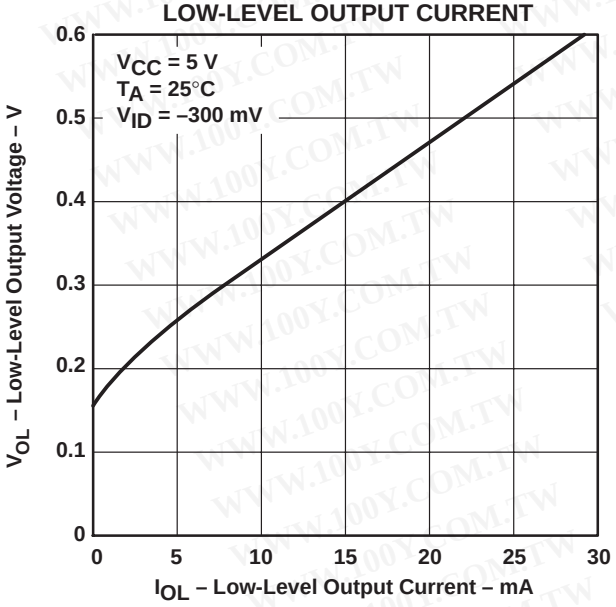


Figure 14

RECEIVER
LOW-LEVEL OUTPUT VOLTAGE
vs
FREE-AIR TEMPERATURE

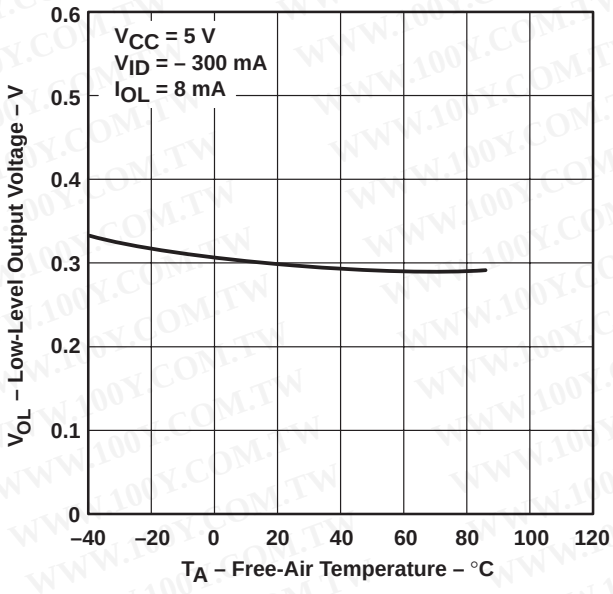


Figure 15

† Operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied.

TYPICAL CHARACTERISTICS†

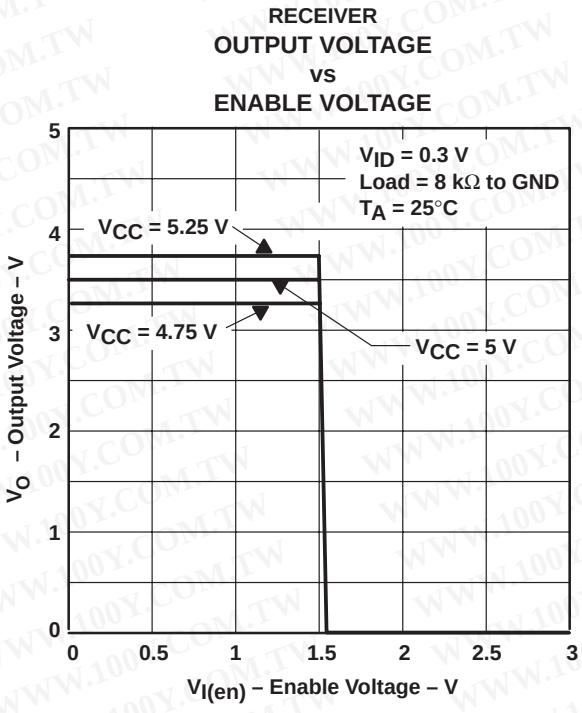


Figure 16

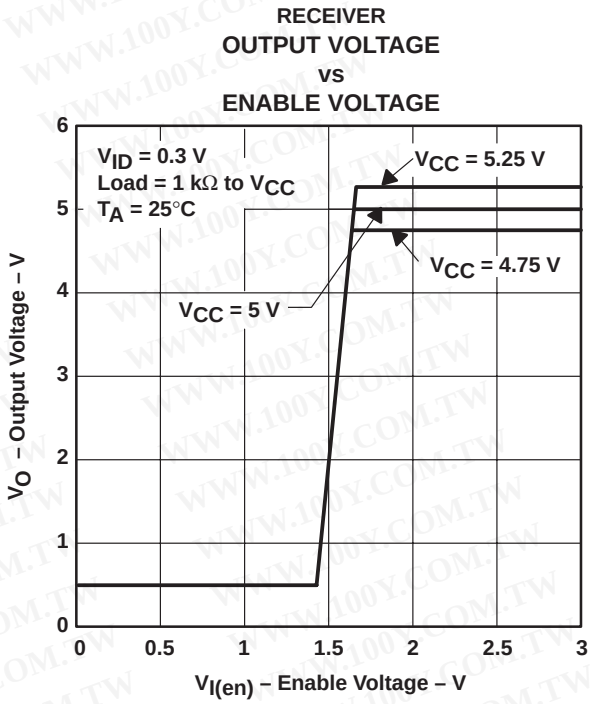
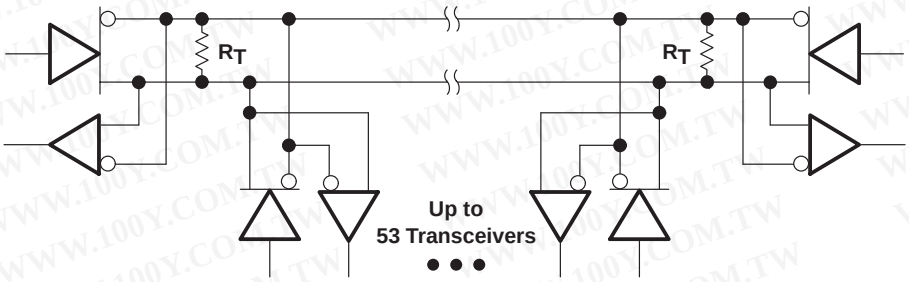


Figure 17

† Operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied.

APPLICATION INFORMATION



NOTE A: The line should terminate at both ends in its characteristic impedance ($R_T = Z_O$). Stub lengths off the main line should be kept as short as possible.

Figure 18. Typical Application Circuit

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
SN65ALS176D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65ALS176DE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65ALS176DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65ALS176DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65ALS176DRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65ALS176DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65ALS176P	OBSOLETE	PDIP	P	8		TBD	Call TI	Call TI
SN75ALS176AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176ADE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176ADG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176ADRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176AP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75ALS176APE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75ALS176BD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176BDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176BDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176BDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176BDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176BDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176BP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75ALS176BPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75ALS176D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176DE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
SN75ALS176DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176DRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75ALS176P	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75ALS176PE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

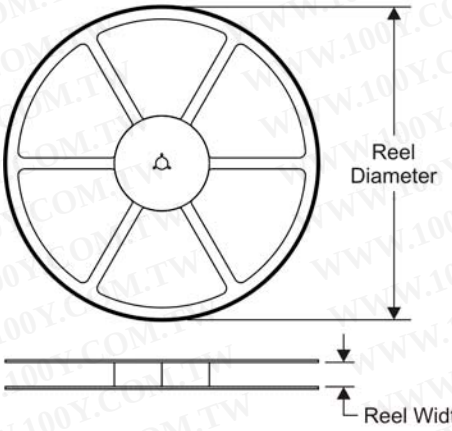
[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

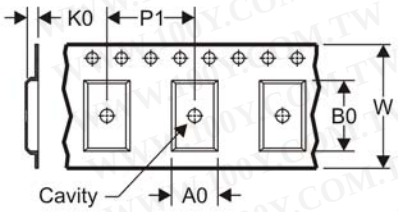
[3] MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

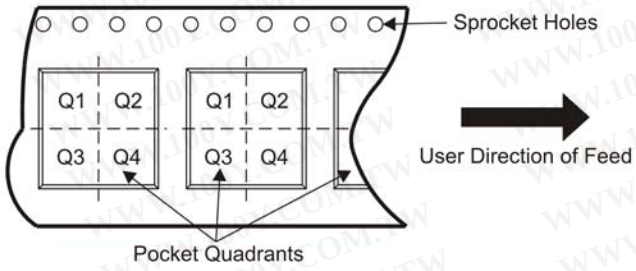


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

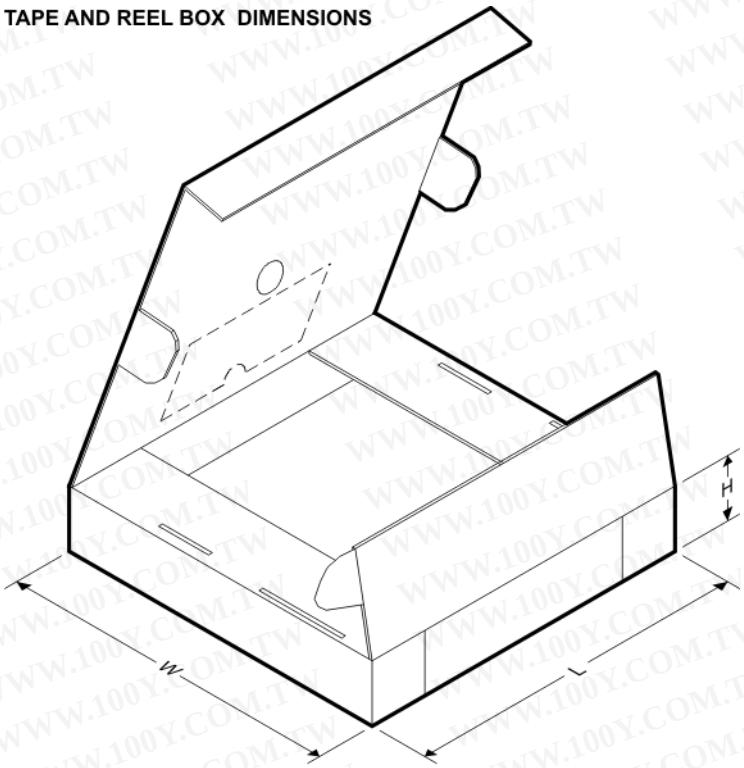
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65ALS176DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75ALS176ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75ALS176BDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75ALS176DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

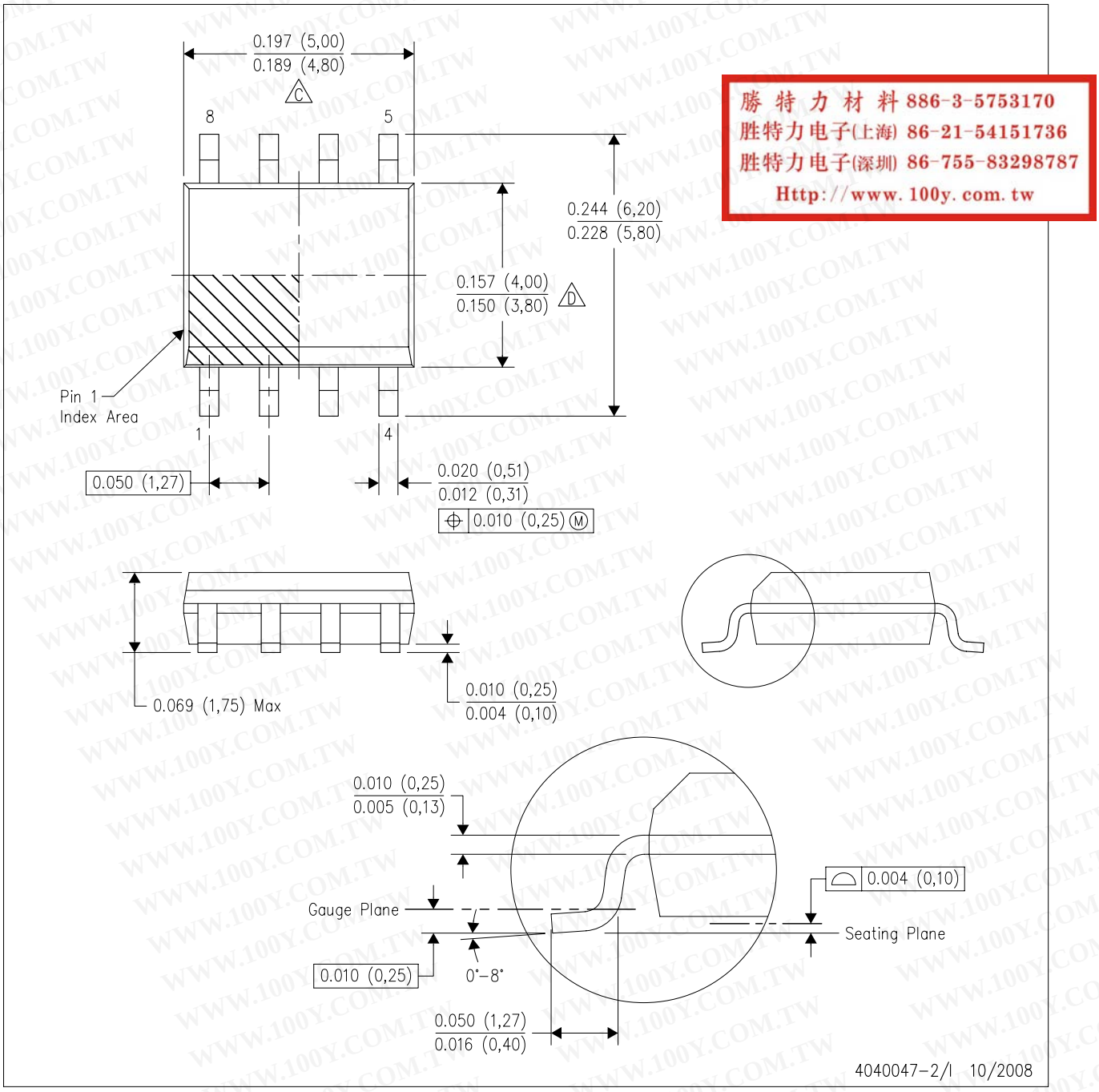
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65ALS176DR	SOIC	D	8	2500	340.5	338.1	20.6
SN75ALS176ADR	SOIC	D	8	2500	340.5	338.1	20.6
SN75ALS176BDR	SOIC	D	8	2500	340.5	338.1	20.6
SN75ALS176DR	SOIC	D	8	2500	340.5	338.1	20.6

D (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
E. Reference JEDEC MS–012 variation AA.

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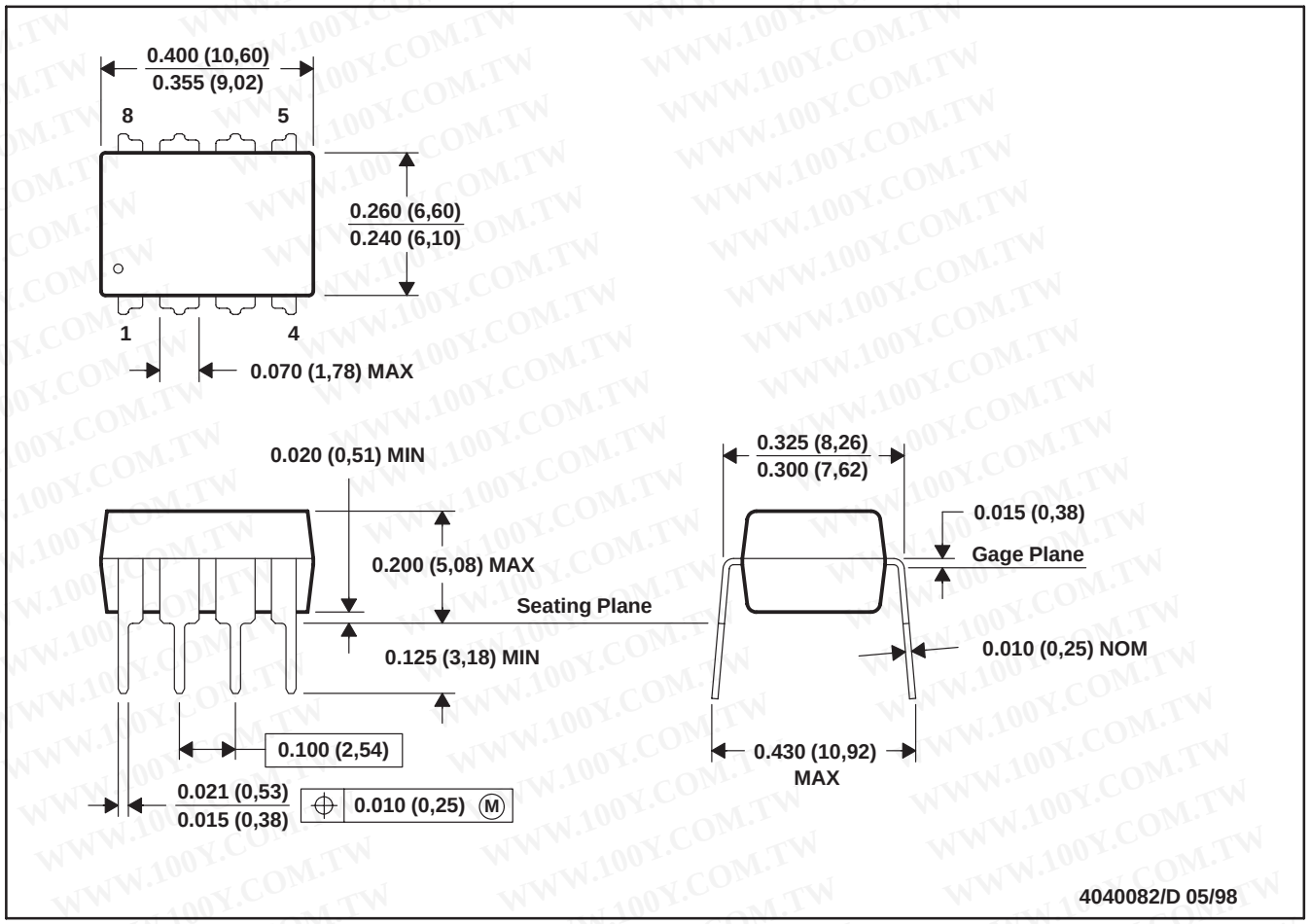
P (R-PDIP-T8) **PLASTIC DUAL-IN-LINE**



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS-001

For the latest package information, go to http://www.ti.com/sc/docs/package/pkg_info.htm